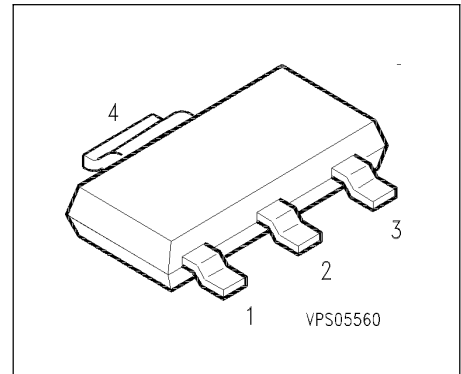


## BSP 319

### SIPMOS® Small-Signal Transistor

- N channel
- Enhancement mode
- Logic Level
- Avalanche rated
- $V_{GS(th)} = 1.2 \dots 2.0 \text{ V}$



Pin 1	Pin 2	Pin 3	Pin 4
G	D	S	D

Type	$V_{DS}$	$I_D$	$R_{DS(on)}$	Package	Marking
BSP 319	50 V	3.8 A	0.07 $\Omega$	SOT-223	BSP 319

Type	Ordering Code	Tape and Reel Information
BSP 319	Q67000-S273	E6327

### Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current $T_A = 29 \text{ }^\circ\text{C}$	$I_D$	3.8	A
DC drain current, pulsed $T_A = 25 \text{ }^\circ\text{C}$	$I_{Dpuls}$	15	
Avalanche energy, single pulse $I_D = 3.8 \text{ A}$ , $V_{DD} = 25 \text{ V}$ , $R_{GS} = 25 \text{ } \Omega$ $L = 6.2 \text{ mH}$ , $T_j = 25 \text{ }^\circ\text{C}$	$E_{AS}$	90	mJ
Gate source voltage	$V_{GS}$	$\pm 20$	V
ESD Sensitivity (HBM) as per MIL-STD 883		Class 1	
Power dissipation $T_A = 25 \text{ }^\circ\text{C}$	$P_{tot}$	1.8	W

**Maximum Ratings**

Parameter	Symbol	Values	Unit
Chip or operating temperature	$T_j$	-55 ... + 150	°C
Storage temperature	$T_{stg}$	-55 ... + 150	
Thermal resistance, chip to ambient air	$R_{thJA}$	≤ 70	K/W
Thermal resistance, junction-soldering point <sup>1)</sup>	$R_{thJS}$	≤ 10	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	

1) Transistor on epoxy pcb 40 mm x 40 mm x 1,5 mm with 6 cm<sup>2</sup> copper area for drain connection

**Electrical Characteristics, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**Static Characteristics**

Drain- source breakdown voltage $V_{GS} = 0\text{ V}, I_D = 0.25\text{ mA}, T_j = 0^\circ\text{C}$	$V_{(BR)DSS}$	50	-	-	V
Gate threshold voltage $V_{GS} = V_{DS}, I_D = 1\text{ mA}$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, T_j = 25^\circ\text{C}$ $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, T_j = 125^\circ\text{C}$	$I_{DSS}$	-	0.1 10	1 100	μA
Gate-source leakage current $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$	$I_{GSS}$	-	10	100	nA
Drain-Source on-state resistance $V_{GS} = 5\text{ V}, I_D = 2.4\text{ A}$	$R_{DS(on)}$	-	0.06	0.07	Ω

**Electrical Characteristics, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**Dynamic Characteristics**

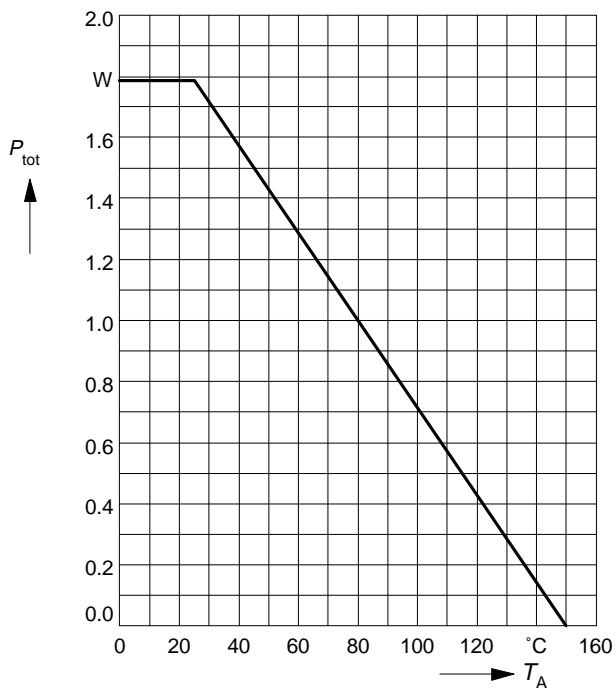
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}, I_D = 2.4 \text{ A}$	$g_{fs}$	3	8	-	S
Input capacitance $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	$C_{iss}$	-	750	1000	pF
Output capacitance $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	$C_{oss}$	-	240	360	
Reverse transfer capacitance $V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	$C_{rss}$	-	120	180	
Turn-on delay time $V_{DD} = 30 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 0.3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_{d(on)}$	-	20	30	ns
Rise time $V_{DD} = 30 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 0.3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_r$	-	55	85	
Turn-off delay time $V_{DD} = 30 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 0.3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_{d(off)}$	-	210	260	
Fall time $V_{DD} = 30 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 0.3 \text{ A}$ $R_{GS} = 50 \Omega$	$t_f$	-	120	160	

**Electrical Characteristics, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Reverse Diode</b>					
Inverse diode continuous forward current $T_A = 25^\circ\text{C}$	$I_S$	-	-	3.8	A
Inverse diode direct current,pulsed $T_A = 25^\circ\text{C}$	$I_{SM}$	-	-	15	
Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = 7.6\text{ A}, T_j = 25^\circ\text{C}$	$V_{SD}$	-	0.95	1.3	V
Reverse recovery time $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	$t_{rr}$	-	50	-	ns
Reverse recovery charge $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$	$Q_{rr}$	-	0.07	-	$\mu\text{C}$

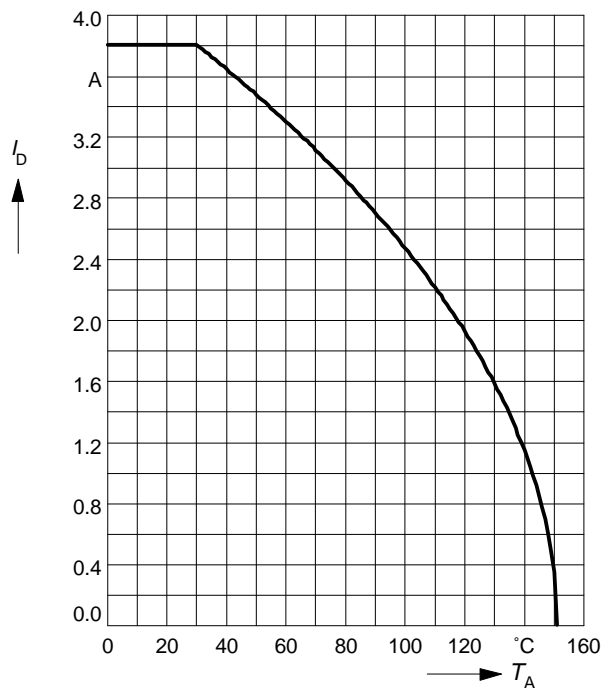
**Power dissipation**

$P_{tot} = f(T_A)$



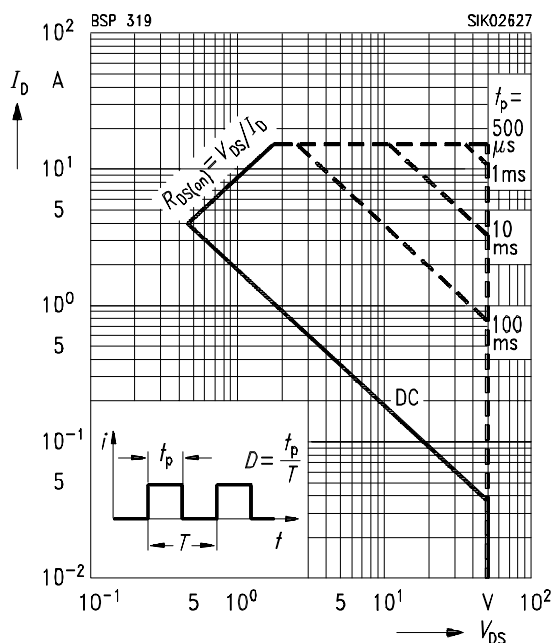
**Drain current**

$I_D = f(T_A)$   
parameter:  $V_{GS} \geq 5 \text{ V}$



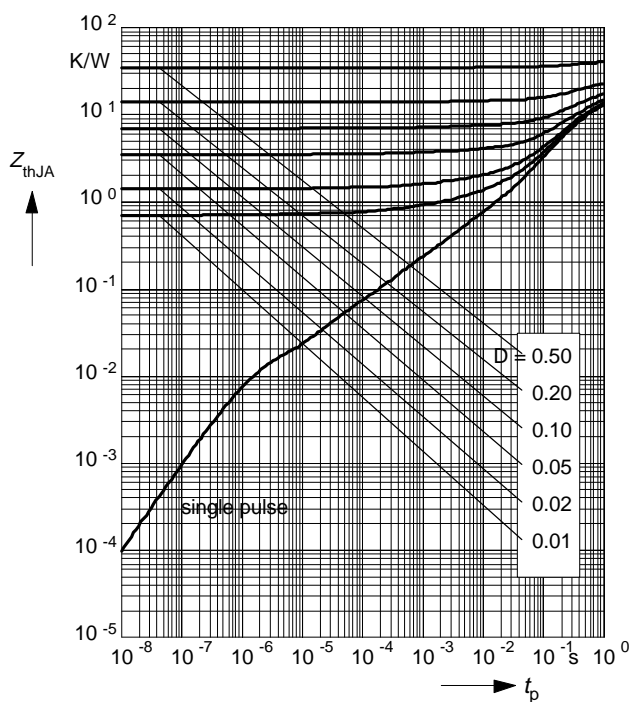
**Safe operating area  $I_D = f(V_{DS})$**

parameter :  $D = 0, T_C = 25^\circ\text{C}$



**Transient thermal impedance**

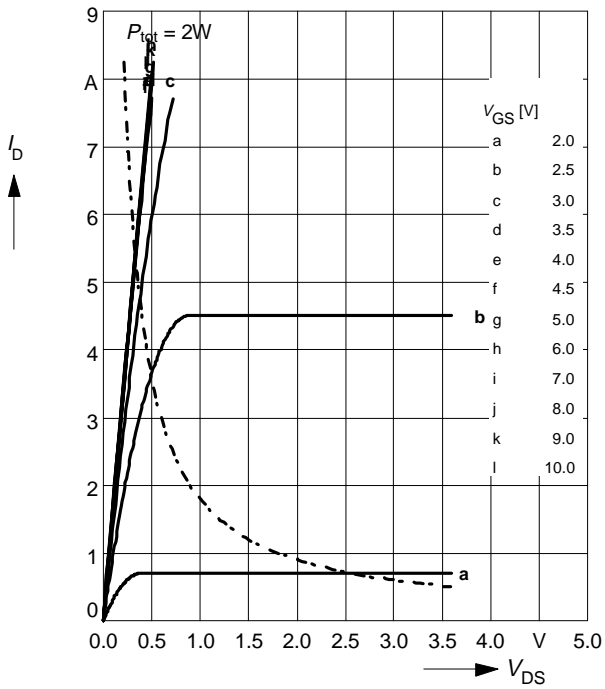
$Z_{thJA} = f(t_p)$   
parameter:  $D = t_p / T$



**Typ. output characteristics**

$I_D = f(V_{DS})$

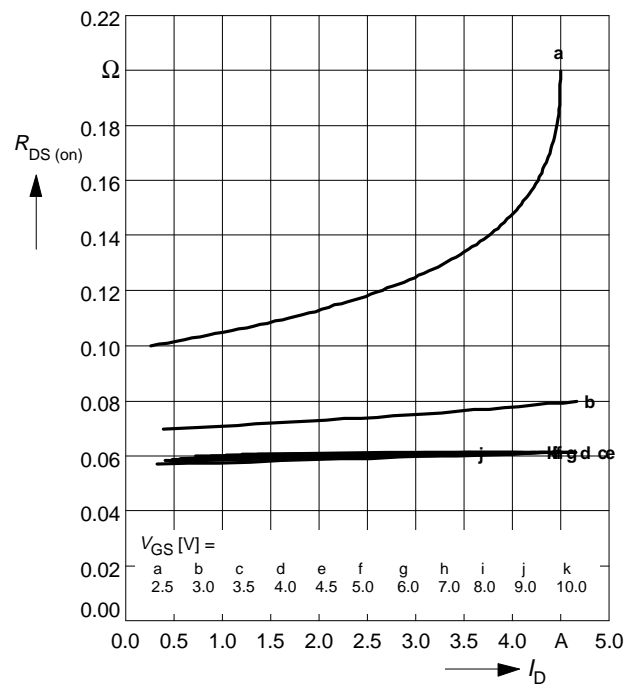
parameter:  $t_p = 80 \mu s$ ,  $T_j = 25 \text{ }^\circ\text{C}$



**Typ. drain-source on-resistance**

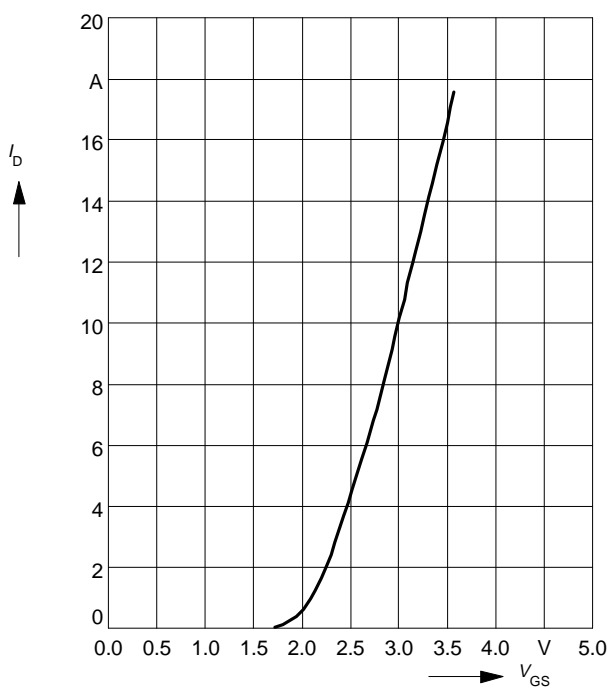
$R_{DS(on)} = f(I_D)$

parameter:  $t_p = 80 \mu s$ ,  $T_j = 25 \text{ }^\circ\text{C}$



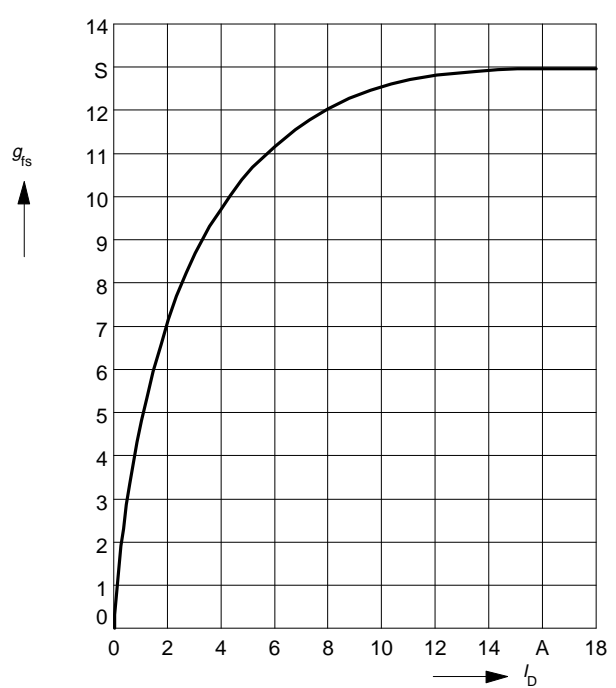
**Typ. transfer characteristics**  $I_D = f(V_{GS})$

parameter:  $t_p = 80 \mu s$



**Typ. forward transconductance**  $g_{fs} = f(I_D)$

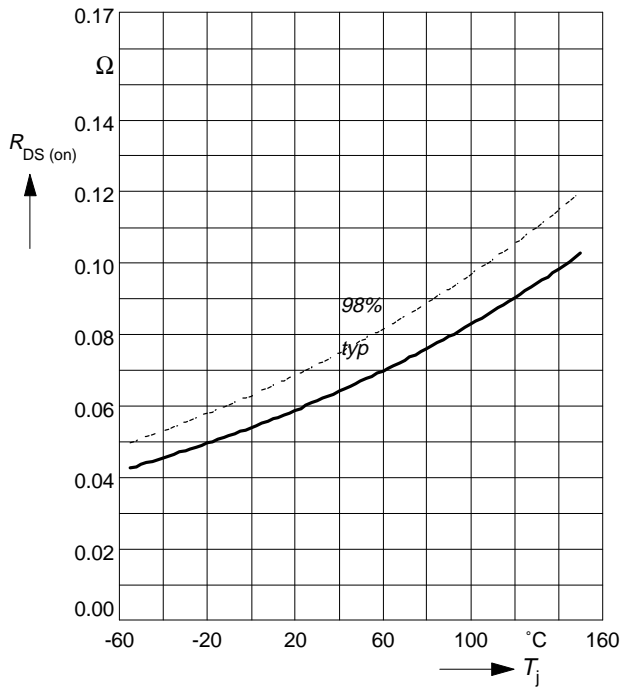
parameter:  $t_p = 80 \mu s$ ,



**Drain-source on-resistance**

$$R_{DS(on)} = f(T_j)$$

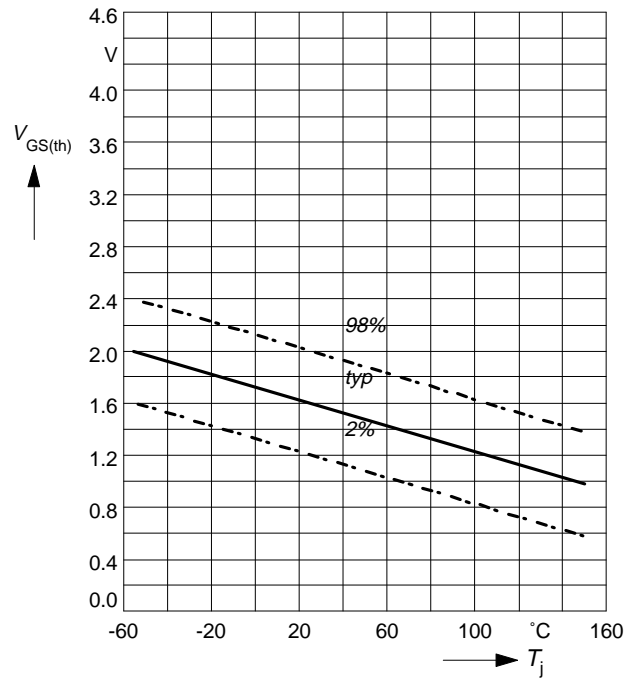
parameter:  $I_D = 2.4 \text{ A}$ ,  $V_{GS} = 5 \text{ V}$



**Gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

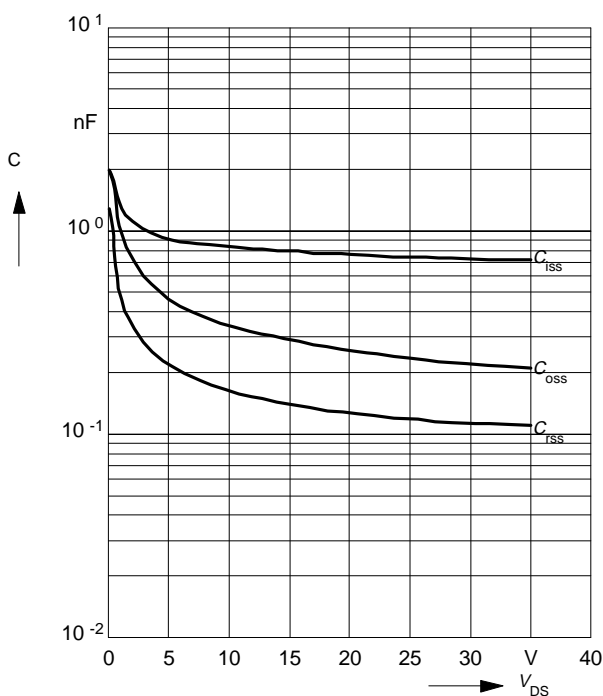
parameter:  $V_{GS} = V_{DS}$ ,  $I_D = 1 \text{ mA}$



**Typ. capacitances**

$$C = f(V_{DS})$$

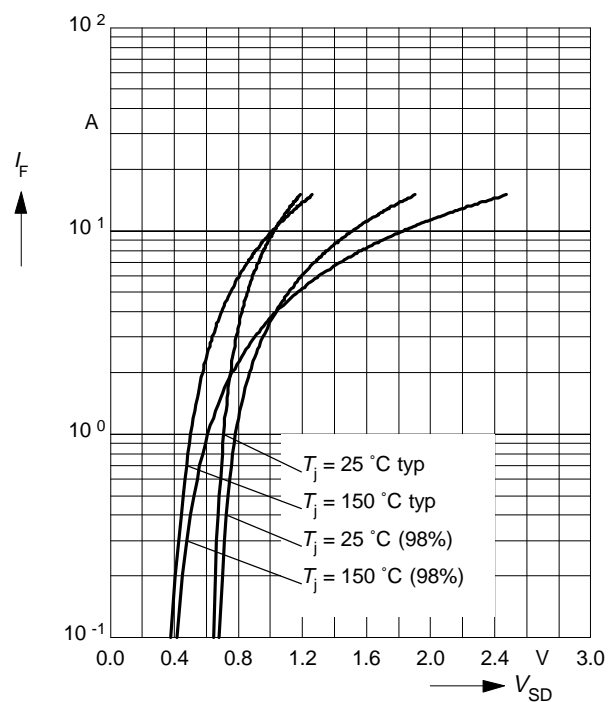
parameter:  $V_{GS} = 0 \text{ V}$ ,  $f = 1 \text{ MHz}$



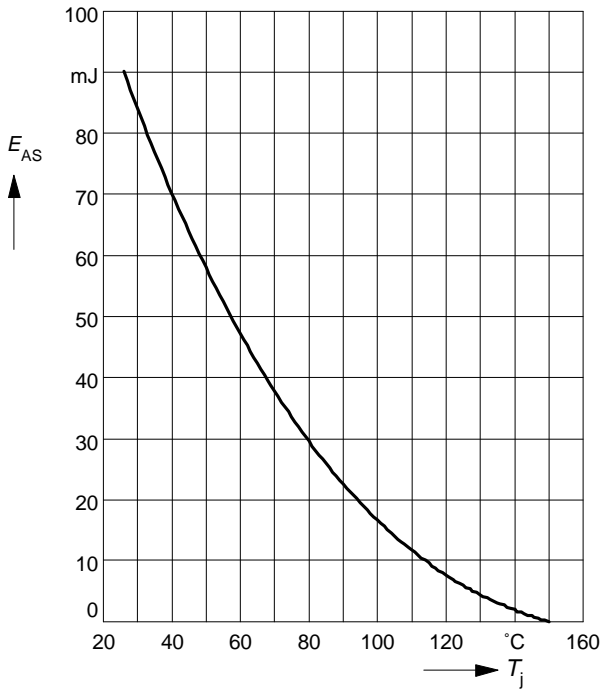
**Forward characteristics of reverse diode**

$$I_F = f(V_{SD})$$

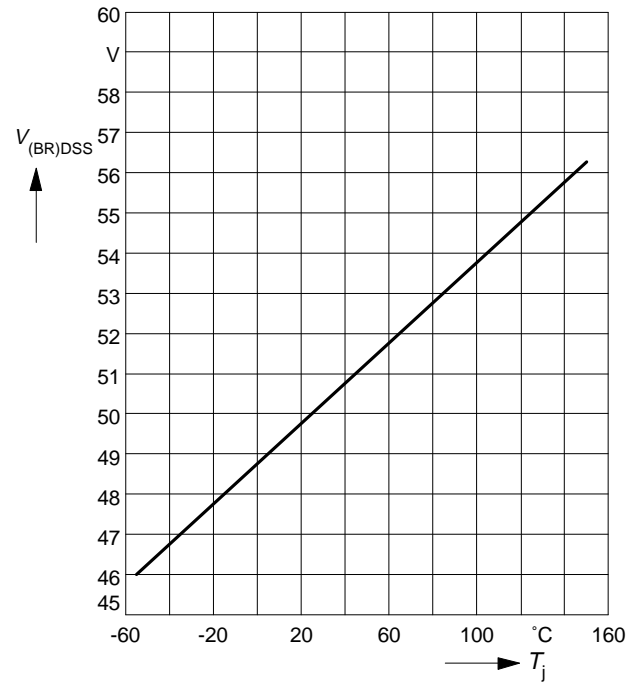
parameter:  $T_j, t_p = 80 \mu\text{s}$



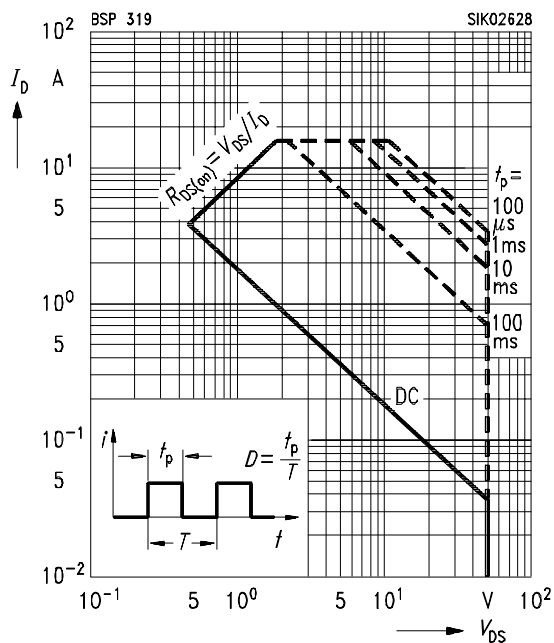
**Avalanche energy**  $E_{AS} = f(T_j)$   
 parameter:  $I_D = 3.8 \text{ A}$ ,  $V_{DD} = 25 \text{ V}$   
 $R_{GS} = 25 \Omega$ ,  $L = 6.2 \text{ mH}$



**Drain-source breakdown voltage**  
 $V_{(BR)DSS} = f(T_j)$



**Safe operating area**  $I_D = f(V_{DS})$   
 parameter :  $D = 0.01$ ,  $T_C = 25^\circ\text{C}$



This datasheet has been downloaded from:

[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

[LittleDiode.com](http://LittleDiode.com)

Looking forward to providing you with the best possible service.